

**Preliminary datasheet**  
**62 mm C-Series module with CoolSiC™ Trench MOSFET**

**Features**

- Electrical features
  - $V_{DSS} = 1200\text{ V}$
  - $I_{DN} = 560\text{ A} / I_{DRM} = 1120\text{ A}$
  - High current density
  - Low switching losses
- Mechanical features
  - 4 kV AC 1 min insulation

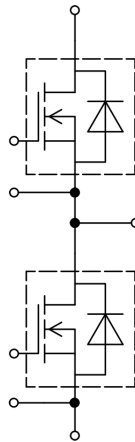
**Potential applications**

- UPS systems
- Solar applications
- DC/DC converter
- High-frequency switching application
- Energy storage systems
- DC charger for EV

**Product validation**

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

**Description**



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## 1 Package

**Table 1** Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50 \text{ Hz}$ , $t = 60 \text{ s}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	29.0	mm
Creepage distance	$d_{Creep}$	terminal to terminal	23.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	23.0	mm
Clearance	$d_{Clear}$	terminal to terminal	11.0	mm
Comparative tracking index	$CTI$		> 400	
Relative thermal index (electrical)	$RTI$	housing	140	°C

**Table 2** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{sCE}$			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$ , per switch		0.465		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for module mounting	$M$	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	$M$	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	$G$			340		g

## 2 MOSFET

**Table 3** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	$V_{DSS}$	$T_{vj} = 25 \text{ °C}$	1200	V
Implemented drain current	$I_{DN}$		560	A
Continuous DC drain current	$I_{DDC}$	$T_{vj} = 175 \text{ °C}$ , $V_{GS} = 18 \text{ V}$ $T_C = 115 \text{ °C}$	390	A
Repetitive peak drain current	$I_{DRM}$	verified by design, $t_p$ limited by $T_{vjmax}$	1120	A

(table continues...)

**Table 3 (continued) Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. transient voltage	$V_{GS}$	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	$V_{GS}$		-7/20	V

**Table 4 Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

**Table 5 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 560\text{ A}$	$V_{GS} = 18\text{ V}$ , $T_{vj} = 25\text{ °C}$		1.47		mΩ
			$V_{GS} = 18\text{ V}$ , $T_{vj} = 125\text{ °C}$		2.38		
			$V_{GS} = 18\text{ V}$ , $T_{vj} = 175\text{ °C}$		3.16		
			$V_{GS} = 15\text{ V}$ , $T_{vj} = 25\text{ °C}$		1.77		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 224\text{ mA}$ , $V_{DS} = V_{GS}$ , $T_{vj} = 25\text{ °C}$ , (tested after 1ms pulse at $V_{GS} = +20\text{ V}$ )	3.45	4.3	5.15	V	
Total gate charge	$Q_G$	$V_{DD} = 800\text{ V}$ , $V_{GS} = -3/18\text{ V}$		1.6		μC	
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\text{ °C}$		0.9		Ω	
Input capacitance	$C_{ISS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_{vj} = 25\text{ °C}$		48.4		nF	
Output capacitance	$C_{OSS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_{vj} = 25\text{ °C}$		2.4		nF	
Reverse transfer capacitance	$C_{rSS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_{vj} = 25\text{ °C}$		0.158		nF	
$C_{OSS}$ stored energy	$E_{OSS}$	$V_{DS} = 800\text{ V}$ , $V_{GS} = -3/18\text{ V}$ , $T_{vj} = 25\text{ °C}$		945		μJ	
Drain-source leakage current	$I_{DSS}$	$V_{DS} = 1200\text{ V}$ , $V_{GS} = -3\text{ V}$ , $T_{vj} = 25\text{ °C}$		0.32	660	μA	
Gate-source leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $T_{vj} = 25\text{ °C}$ , $V_{GS} = 20\text{ V}$			400	nA	

**(table continues...)**

**Table 5 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{d\ on}$	$I_D = 560\ A, R_{Gon} = 4.3\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	166		ns
			$T_{vj} = 125\ ^\circ C$	155		
			$T_{vj} = 175\ ^\circ C$	150		
Rise time (inductive load)	$t_r$	$I_D = 560\ A, R_{Gon} = 4.3\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	172		ns
			$T_{vj} = 125\ ^\circ C$	152		
			$T_{vj} = 175\ ^\circ C$	155		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 560\ A, R_{Goff} = 1.8\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	180		ns
			$T_{vj} = 125\ ^\circ C$	196		
			$T_{vj} = 175\ ^\circ C$	204		
Fall time (inductive load)	$t_f$	$I_D = 560\ A, R_{Goff} = 1.8\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	43		ns
			$T_{vj} = 125\ ^\circ C$	44		
			$T_{vj} = 175\ ^\circ C$	45		
Turn-on energy loss per pulse	$E_{on}$	$I_D = 560\ A, V_{DD} = 600\ V, L_\sigma = 10\ nH, V_{GS} = -3/18\ V, R_{Gon} = 4.3\ \Omega, di/dt = 5.9\ kA/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	23.9		mJ
			$T_{vj} = 125\ ^\circ C$	23.1		
			$T_{vj} = 175\ ^\circ C$	23.3		
Turn-off energy loss per pulse	$E_{off}$	$I_D = 560\ A, V_{DD} = 600\ V, L_\sigma = 10\ nH, V_{GS} = -3/18\ V, R_{Goff} = 1.8\ \Omega, dv/dt = 10.7\ kV/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	15		mJ
			$T_{vj} = 125\ ^\circ C$	16.2		
			$T_{vj} = 175\ ^\circ C$	16.7		
Thermal resistance, junction to case	$R_{thJC}$	per MOSFET			0.0830	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per MOSFET, $\lambda_{grease} = 1\ W/(m\cdot K)$		0.0200		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ C$

**Note:** The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj,op} > 150\ ^\circ C$  is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

### 3 Body diode (MOSFET)

**Table 6** Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	$I_{SD}$	$T_{vj} = 175\text{ °C}$ , $V_{GS} = -3\text{ V}$	$T_C = 115\text{ °C}$	185	A

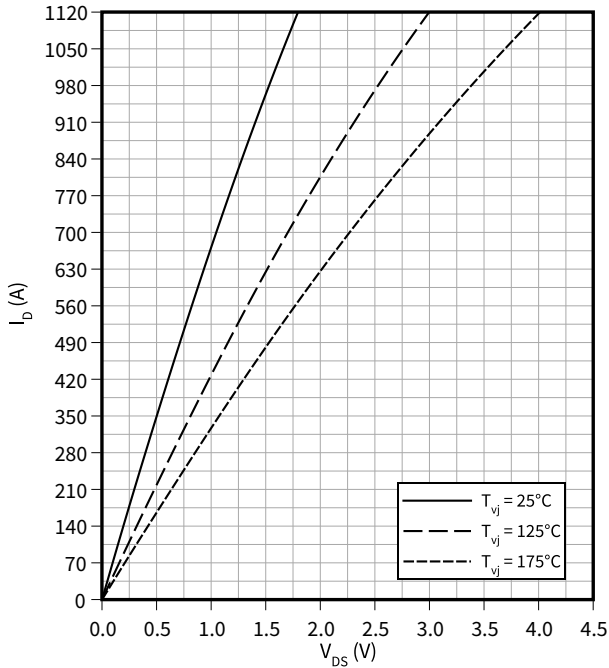
**Table 7** Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	$V_{SD}$	$I_{SD} = 560\text{ A}$ , $V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		4.22	5.59	V
			$T_{vj} = 125\text{ °C}$		3.95		
			$T_{vj} = 175\text{ °C}$		3.85		

## 4 Characteristics diagrams

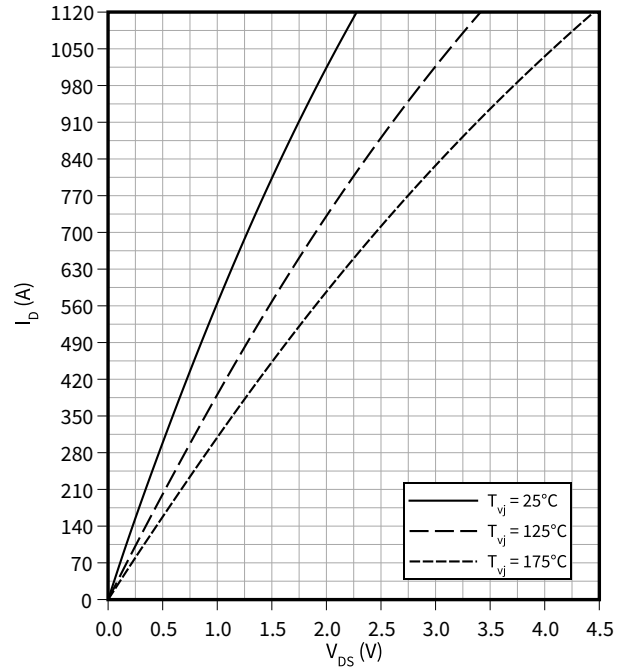
**Output characteristic (typical), MOSFET**

$I_D = f(V_{DS})$   
 $V_{GS} = 18\text{ V}$



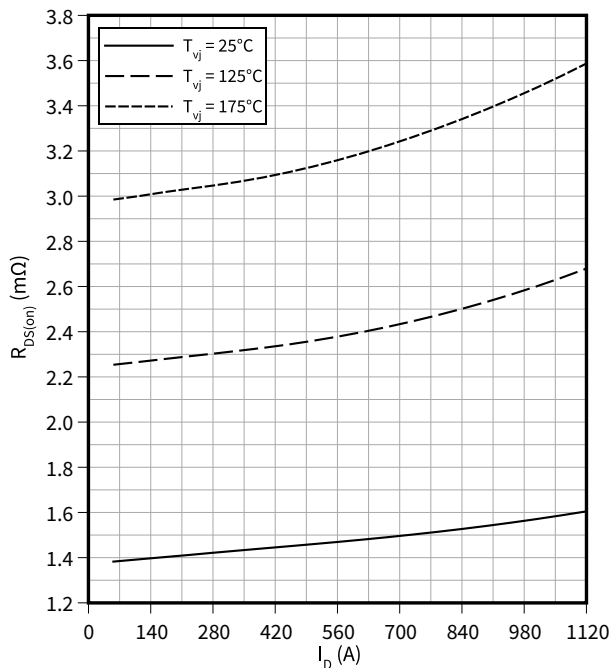
**Output characteristic (typical), MOSFET**

$I_D = f(V_{DS})$   
 $V_{GS} = 15\text{ V}$



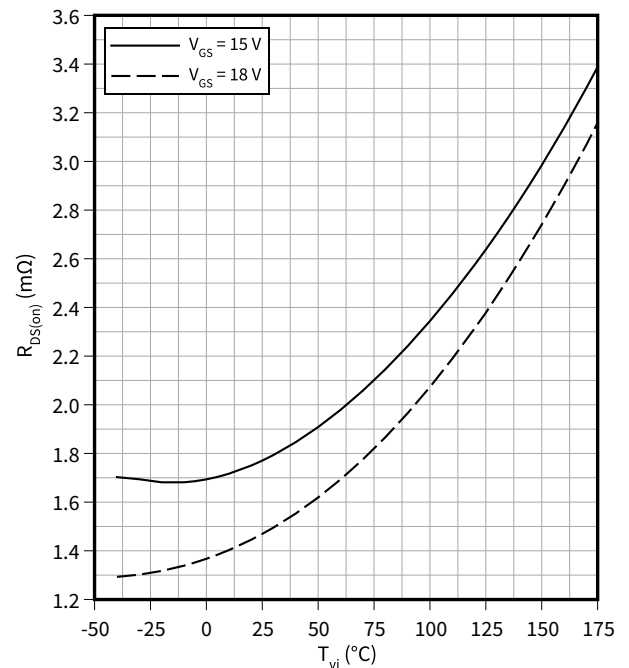
**Drain source on-resistance (typical), MOSFET**

$R_{DS(on)} = f(I_D)$   
 $V_{GS} = 18\text{ V}$



**Drain source on-resistance (typical), MOSFET**

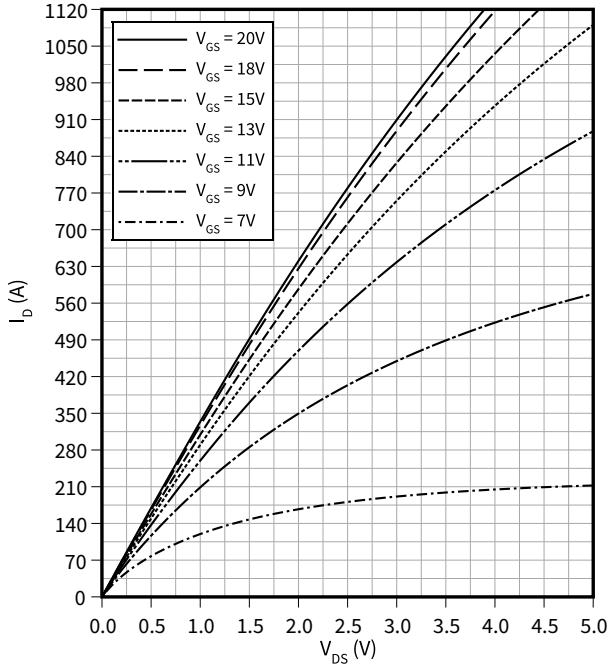
$R_{DS(on)} = f(T_{vj})$   
 $I_D = 560\text{ A}$



4 Characteristics diagrams

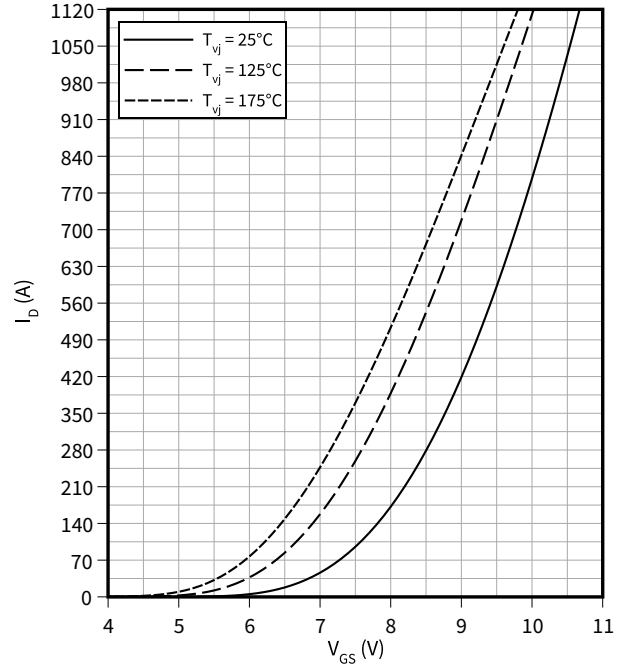
**Output characteristic field (typical), MOSFET**

$I_D = f(V_{DS})$   
 $T_{vj} = 175\text{ °C}$



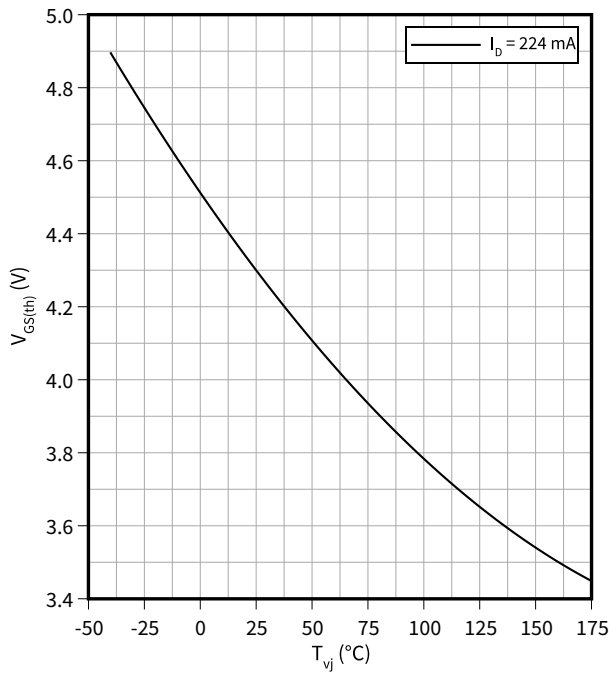
**Transfer characteristic (typical), MOSFET**

$I_D = f(V_{GS})$   
 $V_{DS} = 20\text{ V}$



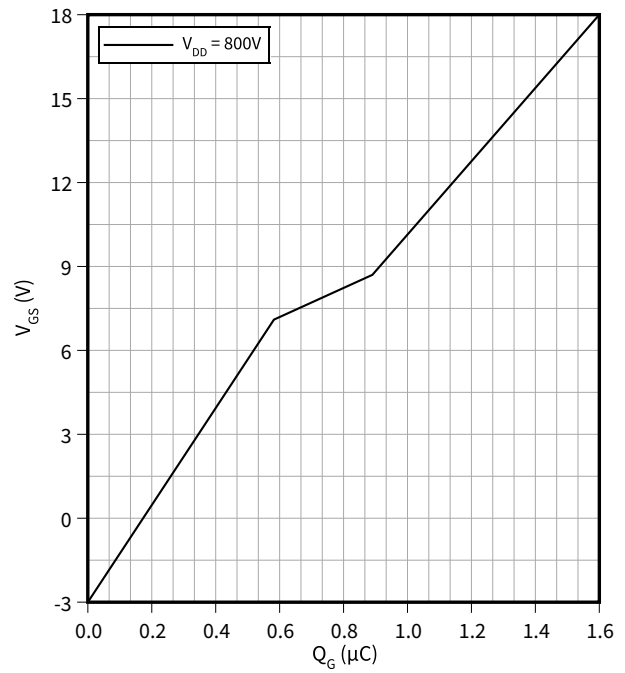
**Gate-source threshold voltage (typical), MOSFET**

$V_{GS(th)} = f(T_{vj})$   
 $V_{GS} = V_{DS}$



**Gate charge characteristic (typical), MOSFET**

$V_{GS} = f(Q_G)$   
 $I_D = 560\text{ A}, T_{vj} = 25\text{ °C}$



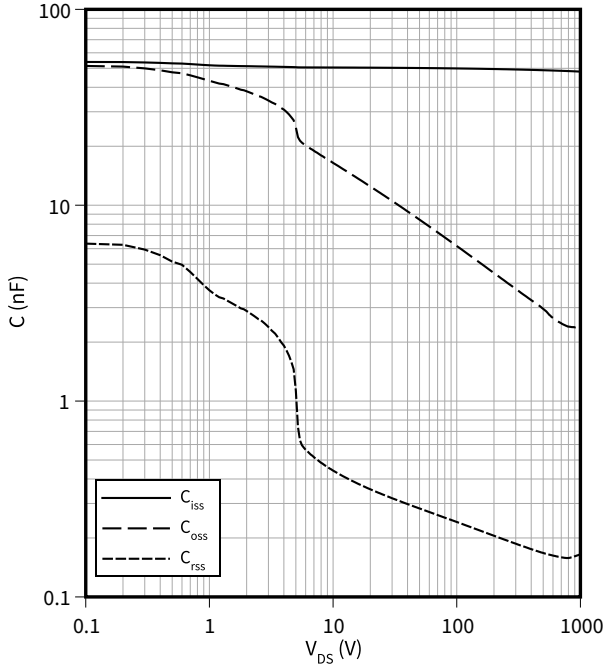


4 Characteristics diagrams

**Capacity characteristic (typical), MOSFET**

$C = f(V_{DS})$

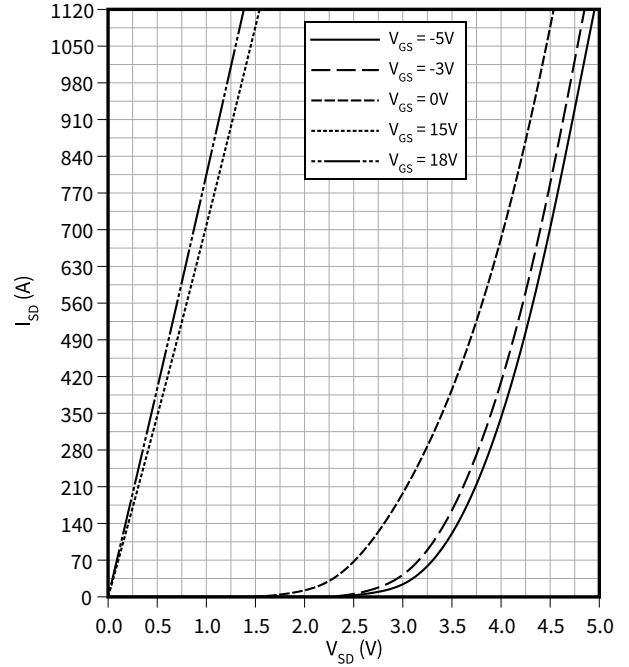
$T_{vj} = 25\text{ °C}, V_{GS} = 0\text{ V}, f = 100\text{ kHz}$



**Forward characteristic body diode (typical), MOSFET**

$I_{SD} = f(V_{SD})$

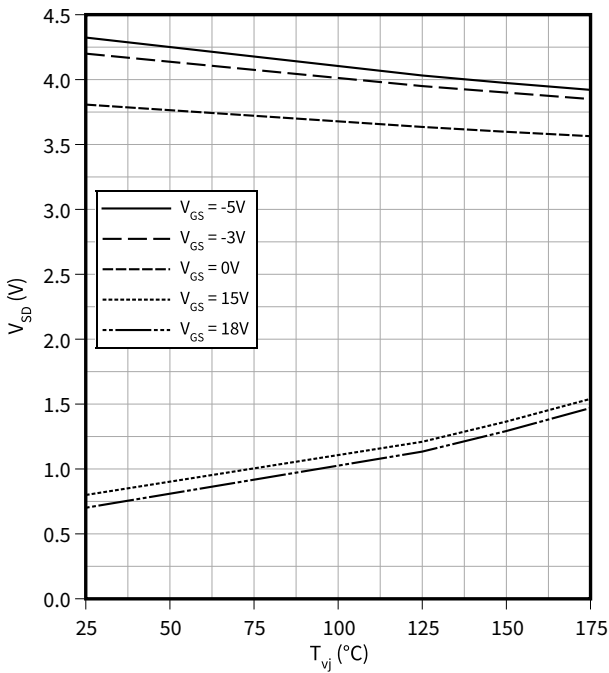
$T_{vj} = 25\text{ °C}$



**Forward voltage of body diode (typical), MOSFET**

$V_{SD} = f(T_{vj})$

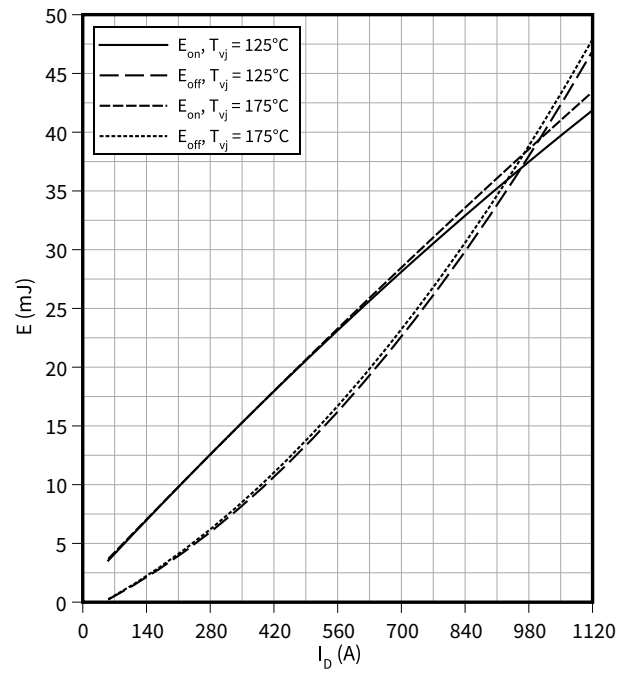
$I_{SD} = 560\text{ A}$



**Switching losses (typical), MOSFET**

$E = f(I_D)$

$R_{Goff} = 1.8\ \Omega, R_{Gon} = 4.3\ \Omega, V_{DD} = 600\text{ V}, V_{GS} = -3/18\text{ V}$

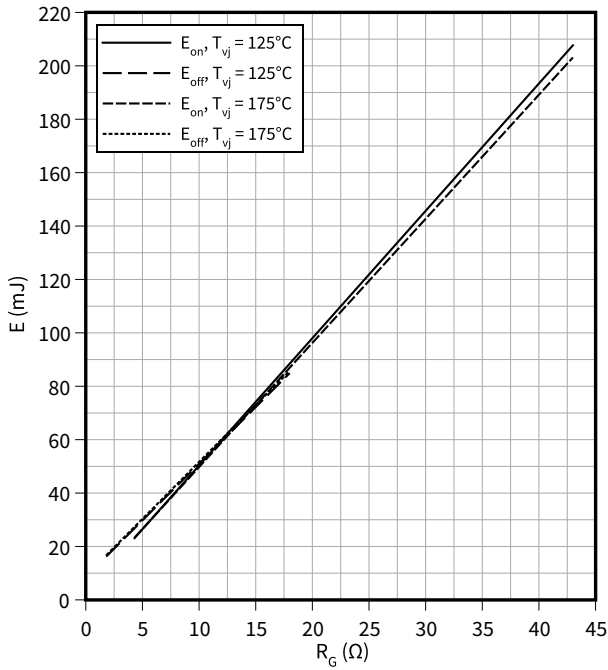


4 Characteristics diagrams

**Switching losses (typical), MOSFET**

$E = f(R_G)$

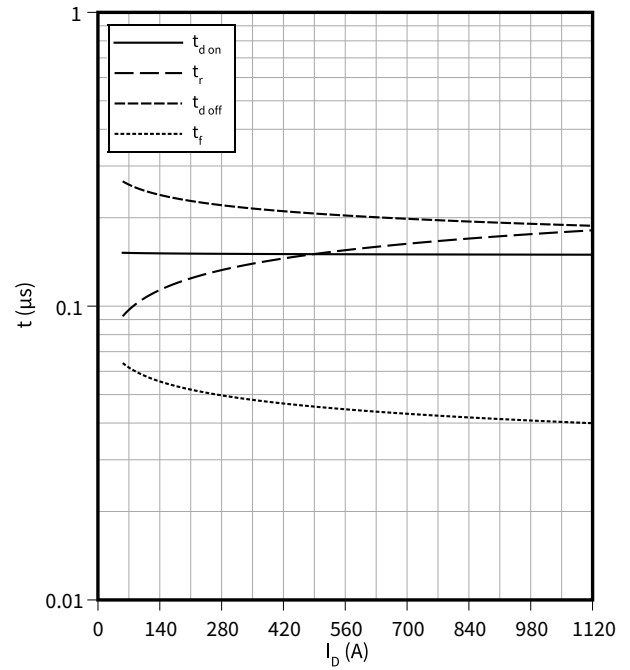
$V_{DD} = 600\text{ V}, I_D = 560\text{ A}, V_{GS} = -3/18\text{ V}$



**Switching times (typical), MOSFET**

$t = f(I_D)$

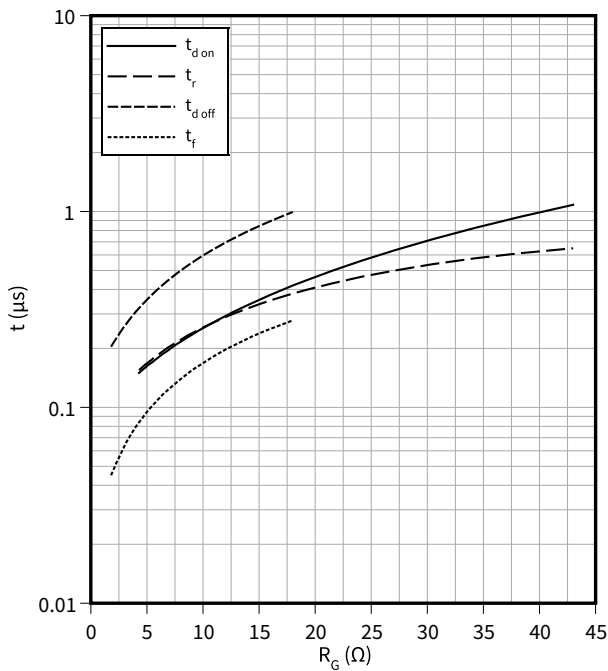
$R_{Goff} = 1.8\ \Omega, R_{Gon} = 4.3\ \Omega, V_{DD} = 600\text{ V}, T_{vj} = 175\text{ }^\circ\text{C}, V_{GS} = -3/18\text{ V}$



**Switching times (typical), MOSFET**

$t = f(R_G)$

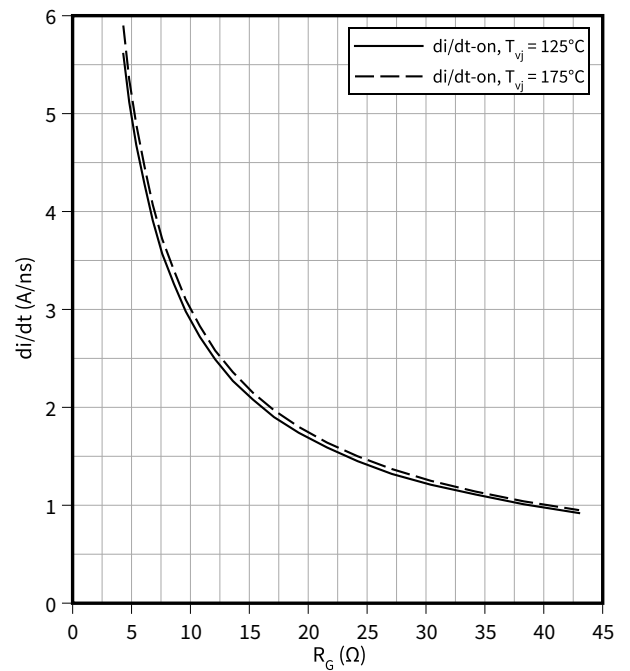
$V_{DD} = 600\text{ V}, I_D = 560\text{ A}, T_{vj} = 175\text{ }^\circ\text{C}, V_{GS} = -3/18\text{ V}$



**Current slope (typical), MOSFET**

$di/dt = f(R_G)$

$V_{DD} = 600\text{ V}, I_D = 560\text{ A}, V_{GS} = -3/18\text{ V}$

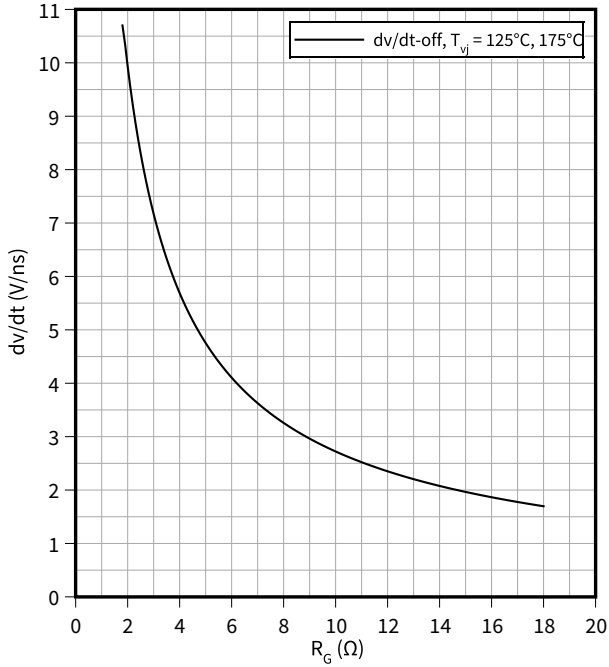


4 Characteristics diagrams

**Voltage slope (typical), MOSFET**

$dv/dt = f(R_G)$

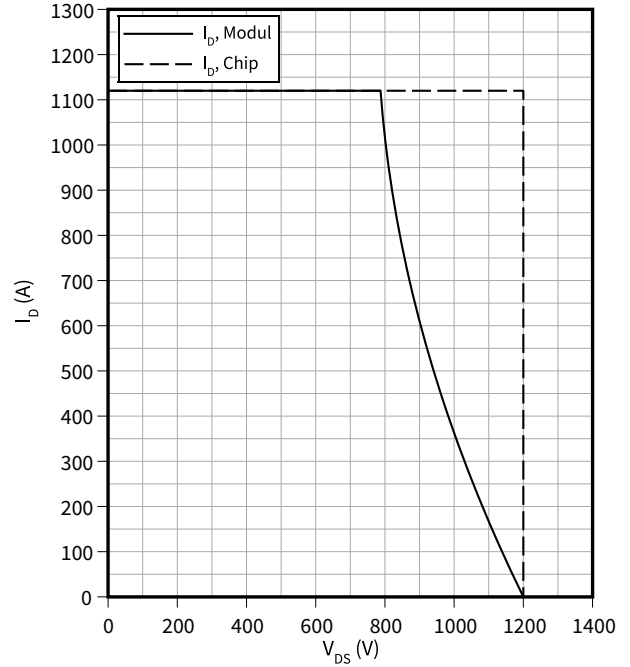
$V_{DD} = 600\text{ V}, I_D = 560\text{ A}, V_{GS} = -3/18\text{ V}$



**Reverse bias safe operating area (RBSOA), MOSFET**

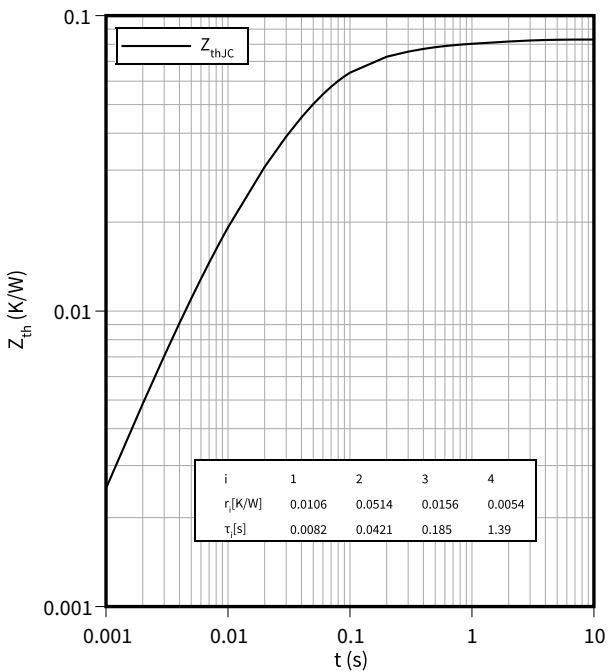
$I_D = f(V_{DS})$

$R_{Goff} = 1.8\ \Omega, T_{vj} = 175\ ^\circ\text{C}, V_{GS} = -3/18\text{ V}$



**Transient thermal impedance, MOSFET**

$Z_{th} = f(t)$



## 5 Circuit diagram

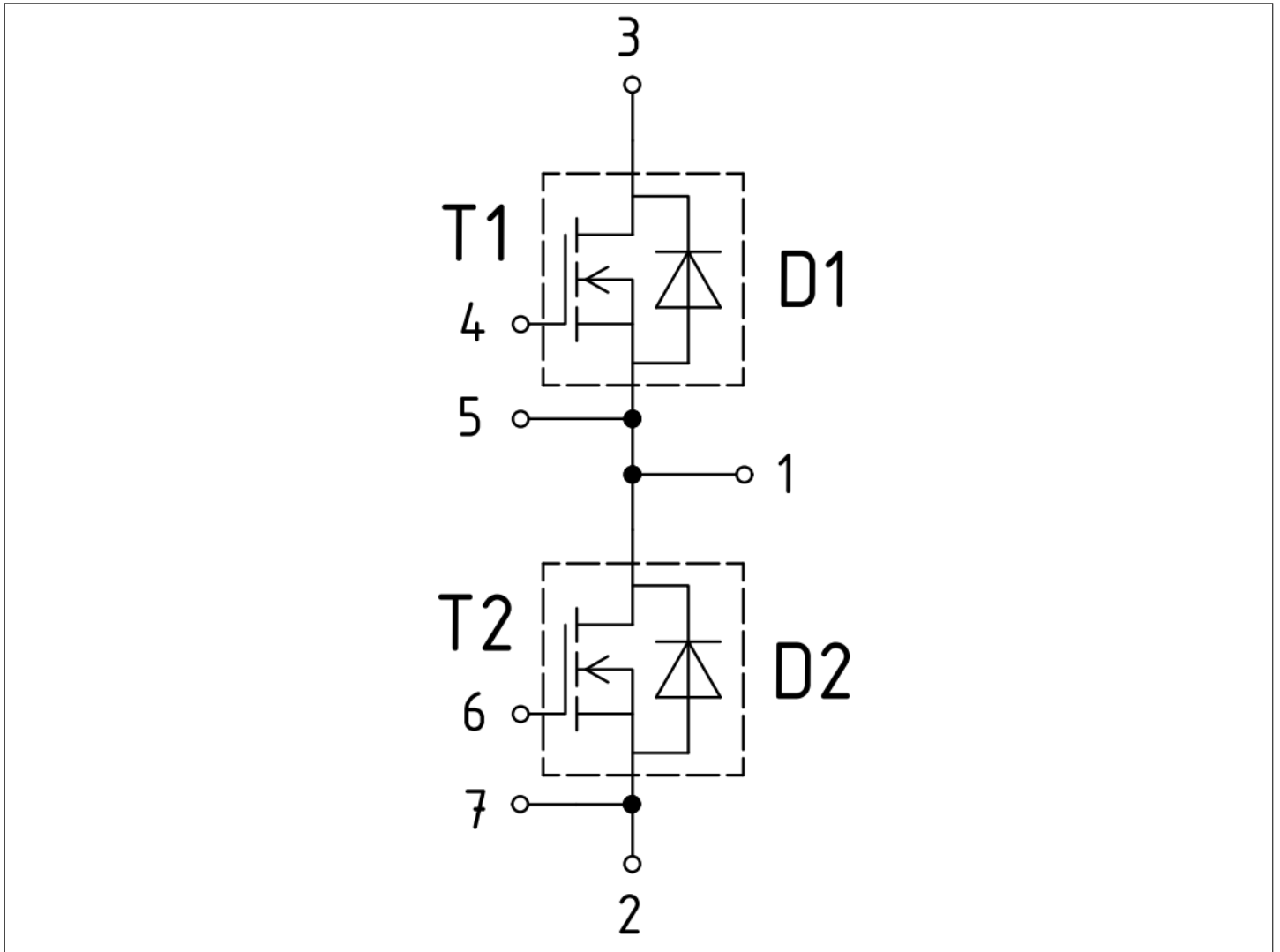
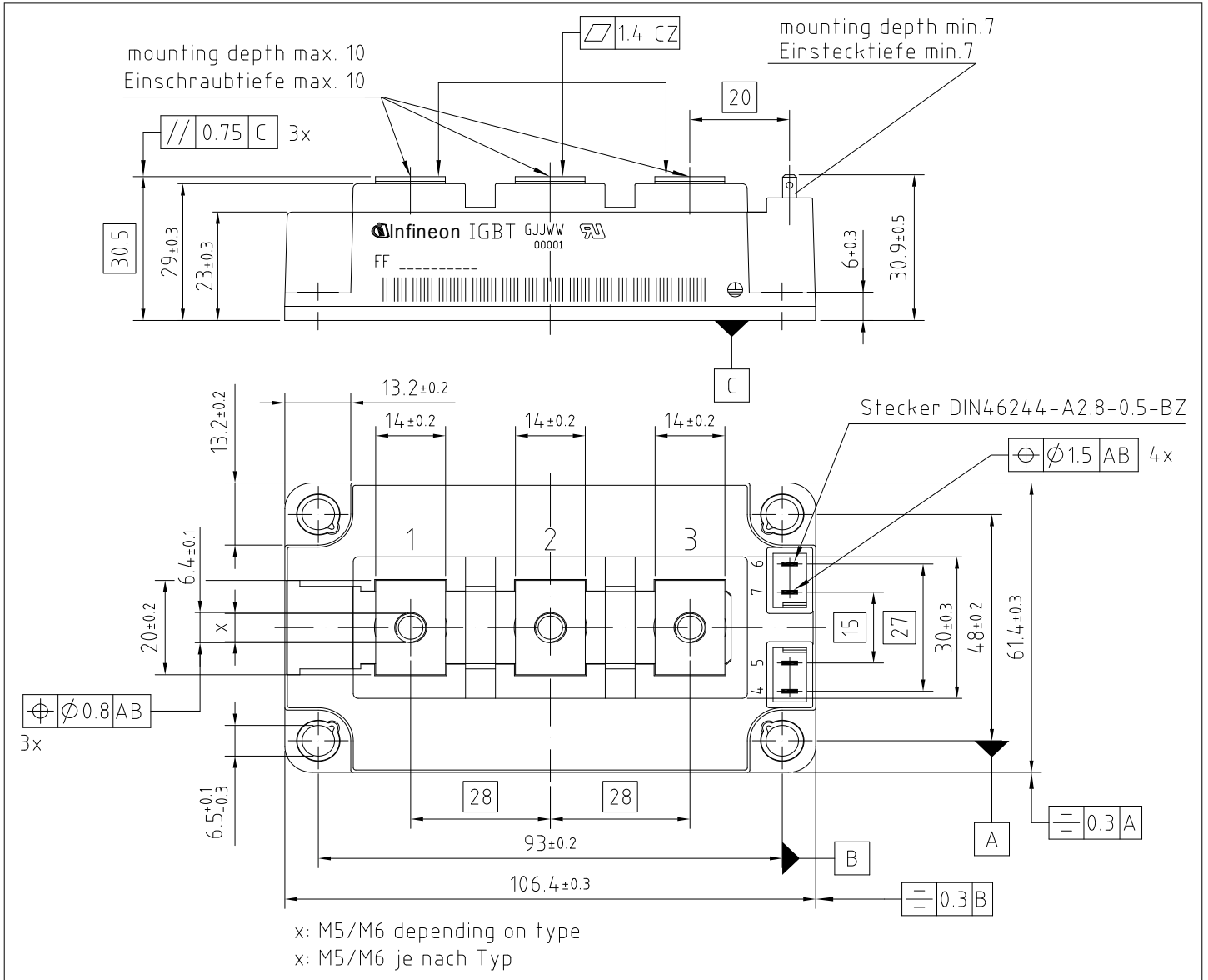



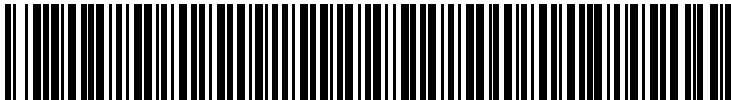
Figure 1

**6 Package outlines**



**Figure 2**

## 7 Module label code

Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

**Figure 3**

## Revision history

Document revision	Date of release	Description of changes
0.10	2023-01-17	Initial version
0.20	2023-02-21	Preliminary datasheet

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**Document reference**

**IFX-ABF635-002**

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[T554](#) [T582](#) [25.332.4353.1](#) [25.350.1653.0](#) [25.352.1453.0](#) [25.352.1653.0](#) [25.352.2453.0](#) [25.352.5453.1](#) [25.522.3353.0](#) [25.640.5053.0](#)  
[M252532V](#) [M252555](#) [M2550TB400](#) [M471B5673EH1-CH900](#) [M505012F-YEC](#) [TD330N16AOF](#) [B512-2T-YDA](#) [TT215N22KOF](#)  
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[TT425N18KOF](#)